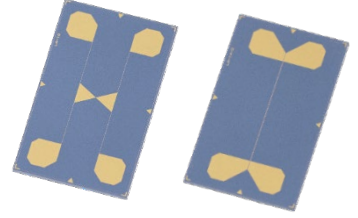
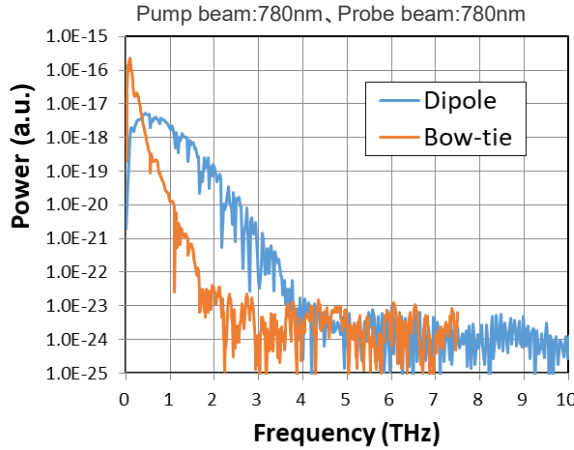


LT-GaAs PCA

Specifications

Emitter : LT-GaAs PCA
Detector : LT-GaAs PCA

Bias	~20Vpp (Dipole, Bowtie)
Pump Power	~20mW@780nm ~30mW@1560nm
Carrier Lifetime	~0.5ps
Probe Power	~20mW@780nm ~30mW@1560nm

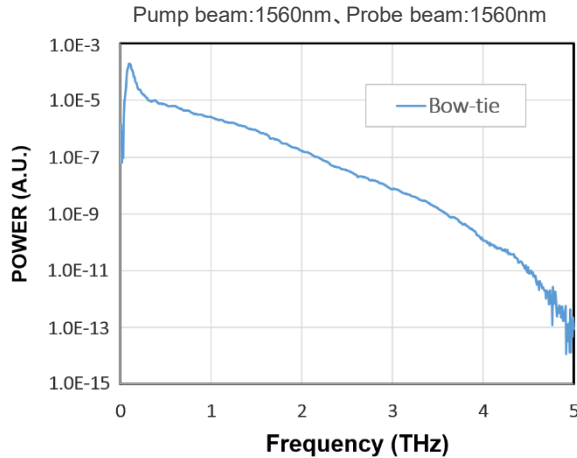


Fe doped InGaAs PCA (For low-bandwidth)

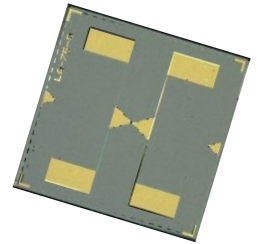
Specifications

Emitter : Fe doped InGaAs PCA
Detector : LT-GaAs PCA

Bias	~40Vpp (Bowtie)
Pump Power	~20mW@1560nm
Dynamic Range	80dB over
Probe Power	~20mW@1560nm



New Release



Epitaxial Wafer Grown by MBE

LT-GaAs Wafer

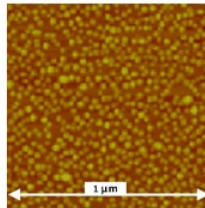
Carrier Lifetime	< 0.5ps
Resistivity	> 10 ⁵ Ωcm
Diameter	2 inch
Thickness	350μm

Quantum Dot Wafer

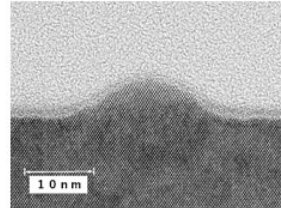
Diameter	2 inch
Material	Ga, In, Al, As, Sb, Si(n), Be(p)

InGaAs Wafer Under development

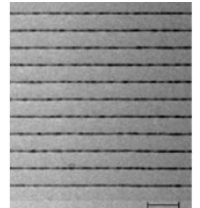
Diameter	2 inch
Thickness	350μm



Quantum Dot surface(AFM)



Quantum Dot (TEM)



Quantum Dot layer(TEM)

Note: The information in this document is subject to change without notice, so please check the latest version when considering it.

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